onsemi

NPN RF Transistor

MMBT5179

Description

This device is designed for use in low noise UHF/VHF amplifiers with collector currents in the 100 μ A to 30 mA range in common emitter or common base mode of operation, and in low frequency drift, high ouput UHF oscillators. Sourced from Process 40.

Features

• This Devices is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	12	V
V_{CBO}	Collector-Base Voltage	20	V
V_{EBO}	Emitter-Base Voltage	2.5	V
Ι _C	Collector Current – Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range (Note 1)	–55 to + 150	°C

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ (Note 3)

Symbol	Characteristic	Max	Unit
PD	Total Device Dissipation Derate above 25°C	225 1.8	MW mW/°C
Reja	Thermal Resistance, Junction to Ambient	556	°C/W

1. These ratings are based on a maximum junction temperature of 150°C.

 These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty cycle operations.

3. Device mounted on FR-4 PCB 1.6" \times 1.6" \times 0.06".



1. Base 2. Emitter 3. Collector

SOT-23 CASE 318-08

MARKING DIAGRAM



3C = Specific Device Code M = Date Code*

I = Date Code* = Pb-Free Package

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(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT5179	SOT-23 (Pb-Free)	3000 / Tape and Real

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

MMBT5179

Symbol	Parameter	Test Conditions	Min	Max	Unit
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage (Note 4)	I _C = 3.0 mA, I _B = 0	12		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1.0 \ \mu A, I_{E} = 0$	20		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	2.5		V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		0.02	μΑ
		$V_{CB} = 15 \text{ V}, \text{ T}_{A} = 150^{\circ}\text{C}$		1.0	μΑ
I CHARACT	ERISTICS				
h _{FE}	DC Current Gain	I_{C} = 3.0 mA, V_{CE} = 1.0 V	25	250	[
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA		0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA		1.0	V
IALL SIGNA	L CHARACTERISTICS				
f _T	Current Gain - Bandwidth Product	I_{C} = 5.0 mA, V_{CE} = 6.0 V, f = 100 MHz	900	2000	MHz
C _{cb}	Collector-Base Capacitance	V_{CB} = 10 V, I _E = 0, f = 0.1 to 1.0 MHz		1.0	pF
h _{fe}	Small-Signal Current Gain	I_{C} = 2.0 mA, V_{CE} = 6 V, f = 1.0 kHz	25	300	1
rb'C _c	Collector Base Time Constant	I_{C} = 2.0 mA, V_{CB} = 6.0 V, f = 31.9 MHz	3.0	14	ps
NF	Noise Figure	I _C = 1.5 mA, V _{CE} = 6.0 V, R _S = 50 Ω, f = 200 MHz		5.0	dB

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

G _{pe}	Amplifier Power Gain	V_{CE} = 6.0 V, I_C = 5.0 mA, f = 200 MHz	15	dB
Po	Power Output	V_{CB} = 10 V, I_{E} = 12 mA, $f \geq$ 500 MHz	20	mW

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

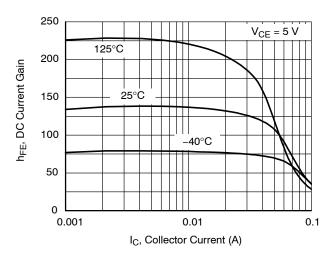
4. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

SPICE MODEL

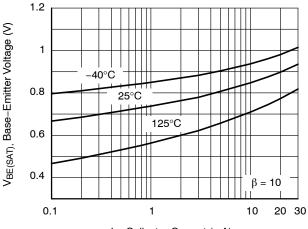
NPN (Is=69.28E-18 Xti=3 Eg=1.11 Vaf=100 Bf=282.1 Ne=1.177 Ise=69.28E-18 Ikf=22.03m Xtb=1.5 Br=1.176 Nc=2 Isc=0 Ikr=0 Rc=4 Cjc=1.042p Mjc=.2468 Vjc=.75 Fc=.5 Cje=1.52p Mje=.3223 Vje=.75 Tr=1.588n Tf=135.6p Itf=.27 Vtf=10 Xtf=30 Rb=10)

MMBT5179

TYPICAL CHARACTERISTICS

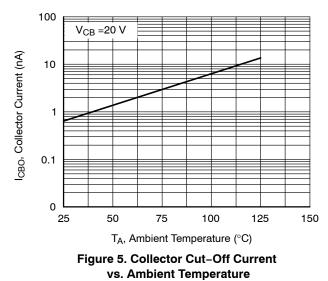






I_C, Collector Current (mA)

Figure 3. Base–Emitter Saturation Voltage vs. Collector Current



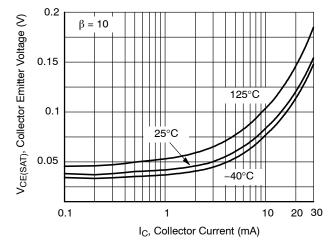


Figure 2. Collector – Emitter Saturation Voltage vs. Collector Current

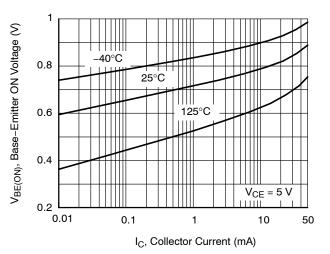
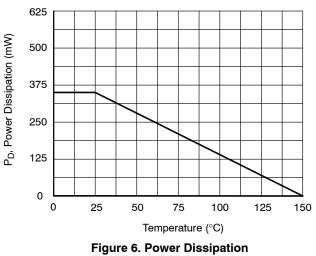


Figure 4. Base–Emitter ON Voltage vs. Collector Current



vs. Ambient Temperature

MMBT5179

TEST CIRCUIT

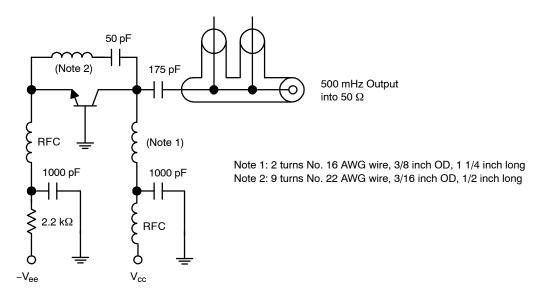


Figure 7. 500 MHz Oscillator Circuit

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